TOSHIBA Power Module

MP7001

1. Maximum Ratings (Ta = 25°C)

Diode

Characteristics	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	600	V
Peak one cycle surge forward current (D1, D2) (50 Hz, non-repetitive)	I _{FSM}	220	А
Forward current	l _F	25	Α
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-40~125	°C

IGBT

Characteristics		Symbol	Rating	Unit
Collector-emitter voltage		V _{CES}	600	V
Gate-emitter voltage		V _{GES}	±20	V
Collector current	DC	IC	30	Α
	1 ms	I _{CP}	60	Α
Collector power dissipation (Tc = 25°C)		P _C	37	W
Junction temperature		Tj	150	°C
Storage temperature range		T _{stg}	-40~125	°C

All system

Characteristics	Symbol	Condition	Rating	Unit
Isolation voltage	V _{ISO}	AC 1 minute	2500	٧

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damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.

• The information contained herein is subject to change without notice.

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2. Electrical Characteristics (Ta = 25°C)

Diode

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Peak forward voltage (1)	V _{FM} (1)	I _F = 12.5 A	_	1.0	1.2	V
Peak forward voltage (2)	V _{FM} (2)	I _F = 30 A		1.20	1.55	V
Repetitive peak reverse Current	I _{RRM}	V _{RRM} = 600 V			10	μΑ
Peak reverse current (D1, D2)	I _{rr}	I _F = 30 A			100	Α
Thermal resistance	R _{th (j-c)}	_		_	3.5	°C/W

IGBT

Cha	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GES}	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$	_	_	±500	nA
Collector cut-off of	current	I _{CES}	V _{CE} = 600 V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cut-	off voltage	V _{GE (OFF)}	$I_C = 30 \text{ mA}, V_{CE} = 5 \text{ V}$	3.0	_	6.0	V
Collector-emitter	saturation voltage	V _{CE} (sat)	I _C = 30 A, V _{GE} = 15 V	_	2.0	2.7	V
Input capacitance		C _{ies}	$V_{CE} = 10 \text{ V}, V_{GE} = 0,$ f = 1 MHz	_	2100	_	pF
	Rise time	t _r	Load resistance	_	0.36	_	
Switching time	Turn-on time	t _{on}	$V_{CC} = 300 \text{ V}, I_{C} = 30 \text{ A}$	_	0.59	_	
	Fall time	t _f	$V_{GE} = \pm 15 \text{ V}, (R_{G} = 56 \Omega)$	_	0.27	0.42	μS
	Turn-off Time	t _{off}	(Note)	_	0.51	_	
Thermal Resistance		R _{th (j-c)}		_	_	3.3	°C/W

3. Mechanical Rating

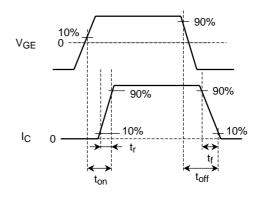
Characteristics	Min	Тур.	Max	Unit
Fastening torque	_	_	1.5	Nm

Note: Switching time test circuit & timing chart

Load Resistance Test Circuit

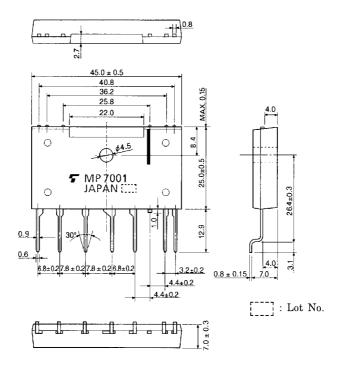
15 V 10 Ω R_G = 56 Ω N 89 = 7 00 N 10 Ω 10

Waveform

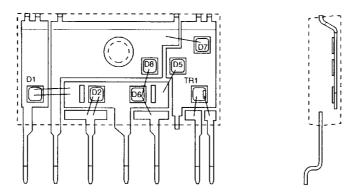




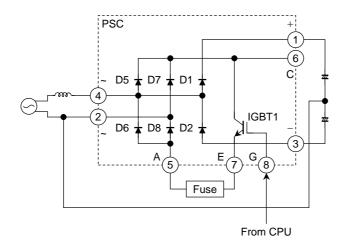
4. Package Dimension



5. Image of Chips Mounting



6. PSC Equivalent Circuit Diagram (including application circuit)



7. Pin Assignment

